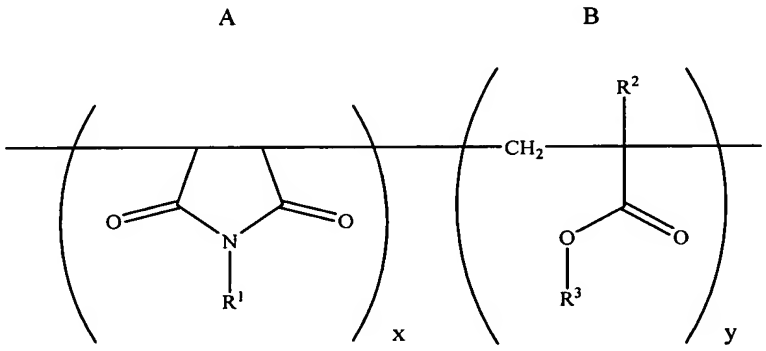
Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-3. (Canceled)

4. (Currently Amended) A bottom anti-reflective coat forming composition for lithography processes in semiconductor device preparation, wherein the bottom anti-reflective coat forming composition comprises resin containing a structural unit comprising maleimide or a derivative thereof~~The bottom anti-reflective coat forming composition according to claim 1~~, wherein the resin comprises the structural unit shown in Formula (2)



Formula (2)

wherein each R^1, R^2 and R^3 is independent of one another; R^1 is hydrogen, halogen, or substituted or unsubstituted C_1-C_{10} alkyl group~~ or benzene derivatives~~; R^2 is hydrogen, halogen or methyl group; R^3 is hydrogen or substituted or unsubstituted C_1-C_{10} alkyl group; x is number 1-10300; and y is number 0-12100, and is the polymer comprising 10-100 mol% of the maleimide structural unit (A) and 90-0 mol% of the (meth)acrylate structural unit (B), based on the sum of the maleimide structural unit (A) and the (meth)acrylate structural unit (B) in the ~~polymer.~~ polymer, and

wherein said composition further comprises crosslinking agent having at least two crosslinking forming functional groups.

5. (Original) The bottom anti-reflective coat forming composition according to claim 4, wherein the maleimide structural unit (A) is 51-95 mol% and the (meth)acrylate structural unit (B) is 49-5 mol% in the structural unit shown in the Formula (2).

6. (Currently Amended) The bottom anti-reflective coat forming composition according ~~claim 3, wherein~~to claim 4, wherein R^1 is hydrogen, halogen or substituted or unsubstituted C_1-C_{10} alkyl group in the structural unit shown in the Formula (1) or the Formula (2).

7. (Canceled)

8. (Currently Amended) ~~The~~ A method of forming ~~the~~ a bottom anti-reflective coating for ~~the~~ lithography ~~process~~ processes in ~~the~~ semiconductor device preparation ~~of semiconductor device~~, comprising applying the bottom anti-reflective coat forming composition according to ~~claim 1~~claim 4 over ~~the~~ a substrate, and then baking.

9. (Currently Amended) ~~The~~ A method of ~~the~~ semiconductor device preparation ~~for semiconductor device~~, comprising:

applying the bottom anti-reflective coat forming composition according to ~~claim 1~~claim 4 over ~~the~~ a substrate,

baking the coated substrate to form a~~forming the~~ bottom anti-reflective coating upon baking,

coating photoresist over said bottom anti-reflective coating,

exposing said substrate to form an image,

transferring the image over the substrate by etching, and

developing and forming integrated circuit elements ~~after transferring the image over the substrate by etching~~.

10. (Currently Amended) The method of ~~the~~ semiconductor device preparation ~~for semiconductor device~~ according to claim 9, wherein exposure is conducted with ~~the~~ light at 193 nm wave-length.